

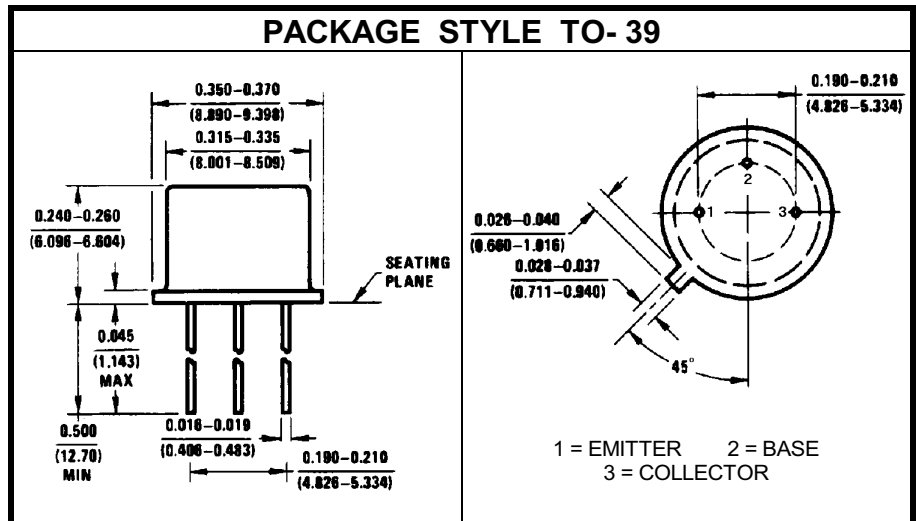
SILICON PNP TRANSISTOR

DESCRIPTION:

The **2N3635** is Designed for General Purpose Amplifier and Switching Applications.

MAXIMUM RATINGS

I_C	300 mA
V_{CE}	-140 V
P_{DISS}	5.0 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+200^\circ\text{C}$
θ_{JC}	35°C/W



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 10\text{ mA}$		-140			V
BV_{CBO}	$I_C = 100\text{ }\mu\text{A}$		-140			V
I_{CBO}	$V_{CB} = -100\text{ V}$				100	nA
BV_{EBO}	$I_E = 10\text{ }\mu\text{A}$		-5.0			V
I_{EBO}	$V_{EB} = -3.0\text{ V}$				50	nA
h_{FE}	$V_{CE} = -10\text{ V}$	$I_C = 100\text{ }\mu\text{A}$	80			---
		$I_C = 1.0\text{ mA}$	90			
		$I_C = 10\text{ mA}$	100			
		$I_C = 50\text{ mA}$	100		300	
		$I_C = 150\text{ mA}$	50			
$V_{CE(SAT)}$	$I_C = 10\text{ mA}$	$I_B = 1.0\text{ mA}$			-0.3	V
	$I_C = 50\text{ mA}$	$I_B = 5.0\text{ mA}$			-0.5	
$V_{BE(SAT)}$	$I_C = 10\text{ mA}$	$I_B = 1.0\text{ mA}$			-0.8	V
	$I_C = 50\text{ mA}$	$I_B = 5.0\text{ mA}$	-0.65		-0.9	
f_t	$V_{CE} = -30\text{ V}$	$I_C = 30\text{ mA}$	$f = 100\text{ MHz}$	200		MHz
h_{fe}	$V_{CE} = -10\text{ V}$	$I_C = 10\text{ mA}$	$f = 1.0\text{ KHz}$	200	1200	---
N_F	$V_{CE} = -10\text{ V}$	$I_C = 500\text{ }\mu$	$f = 1.0\text{ KHz}$			---
t_{on}	$V_{CC} = -100\text{ V}$	$I_C = 50\text{ mA}$	$V_{BE} = 4.0\text{ V}$		400	nS
t_{off}	$V_{CC} = -100\text{ V}$	$I_C = 50\text{ mA}$	$V_{BE} = 4.0\text{ V}$		600	nS
C_{ob}	$V_{CB} = -20\text{ V}$		$f = 100\text{ KHz}$		10	pF
C_{ib}	$V_{EB} = -1.0\text{ V}$		$f = 100\text{ KHz}$		75	pF